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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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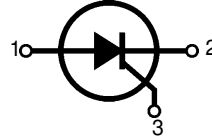
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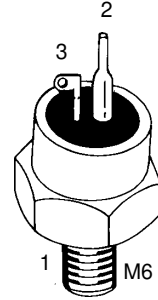
Phase Control Thyristors

$V_{RRM} = 800-1600 \text{ V}$
 $I_{T(RMS)} = 50 \text{ A}$
 $I_{T(AV)M} = 32 \text{ A}$

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
900	800	CS 23-08io2
1300	1200	CS 23-12io2
1700	1600	CS 23-16io2



TO-208AA
(TO-48)



1 = Anode, 2 = Cathode, 3 = Gate

Symbol	Test Conditions	Maximum Ratings
$I_{T(RMS)}$	$T_{VJ} = T_{VJM}$	50 A
$I_{T(AV)M}$	$T_{case} = 85^{\circ}\text{C}; 180^{\circ}$ sine	25 A
	$T_{case} = 69^{\circ}\text{C}; 180^{\circ}$ sine	32 A
I_{TSM}	$T_{VJ} = 45^{\circ}\text{C}; V_R = 0$	t = 10 ms (50 Hz), sine: 450 A t = 8.3 ms (60 Hz), sine: 480 A
	$T_{VJ} = T_{VJM}; V_R = 0$	t = 10 ms (50 Hz), sine: 400 A t = 8.3 ms (60 Hz), sine: 430 A
I^2t	$T_{VJ} = 45^{\circ}\text{C}; V_R = 0$	t = 10 ms (50 Hz), sine: 1010 A ² s t = 8.3 ms (60 Hz), sine: 970 A ² s
	$T_{VJ} = T_{VJM}; V_R = 0$	t = 10 ms (50 Hz), sine: 800 A ² s t = 8.3 ms (60 Hz), sine: 770 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}; f = 50 \text{ Hz}; t_p = 200 \mu\text{s}; V_D = 2/3 V_{DRM}; I_G = 0.3 \text{ A}$	repetitive, $I_T = 75 \text{ A}$: 150 A/ μs
	$di_G/dt = 0.3 \text{ A}/\mu\text{s}$	non repetitive, $I_T = I_{T(AV)M}$: 500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}; R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$: 1000 V/ μs
P_{GM}	$T_{VJ} = T_{VJM}; t_p = 30 \mu\text{s}$	10 W
$P_{G(AV)}$	$I_T = I_{T(AV)M}; t_p = 300 \mu\text{s}$	5 W
V_{RGM}		0.5 W
T_{VJ}		10 V
T_{VJM}		-40...+125 °C
T_{stg}		125 °C
M_d	Mounting torque	-40...+125 °C
		2.7-3.3 Nm
		24-29 lb.in.
Weight		12 g

Features

- Thyristor for line frequencies
- International standard package JEDEC TO-208AA
- Planar glassivated chip
- Long-term stability of blocking currents and voltages

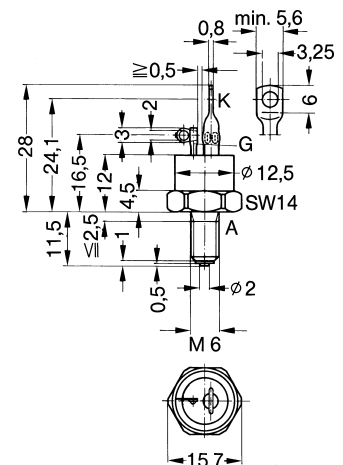
Applications

- Motor control
- Power converter
- AC power controller

Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values	
I_R, I_D	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	3 mA
V_T	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.8 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)		1.0 V
r_T			10 m Ω
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	2.5 V
	$T_{VJ} = -40^\circ\text{C}$	\leq	3.5 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	50 mA
	$T_{VJ} = -40^\circ\text{C}$	\leq	80 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	\leq	0.2 V
I_{GD}		\leq	1 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.15 \text{ A}; di_G/dt = 0.15 \text{ A}/\mu\text{s}$	\leq	200 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	100 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.15 \text{ A}; di_G/dt = 0.15 \text{ A}/\mu\text{s}$	\leq	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 25 \text{ A}, t_p = 300 \mu\text{s}; di/dt = -20 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	60 μs
R_{thJC}	DC current		1.0 K/W
R_{thJH}	DC current		1.61 K/W
d_S	Creepage distance on surface		1.5 mm
d_A	Strike distance through air		1.5 mm
a	Max. acceleration, 50 Hz		50 m/s ²

Accessories:

Nut M6 DIN 439/SW14

Lock washer A6 DIN 128

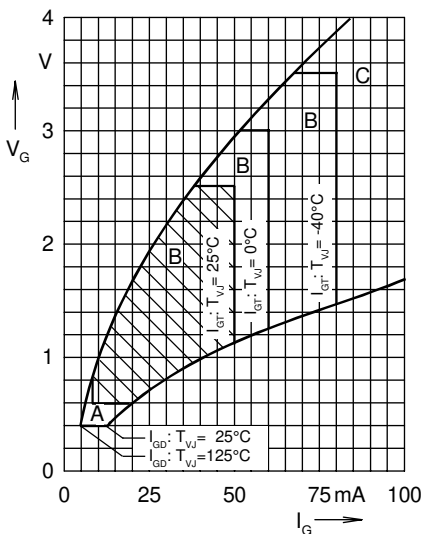


Fig. 1 Gate voltage and gate current
Triggering:
A = no; B = possible; C = safe

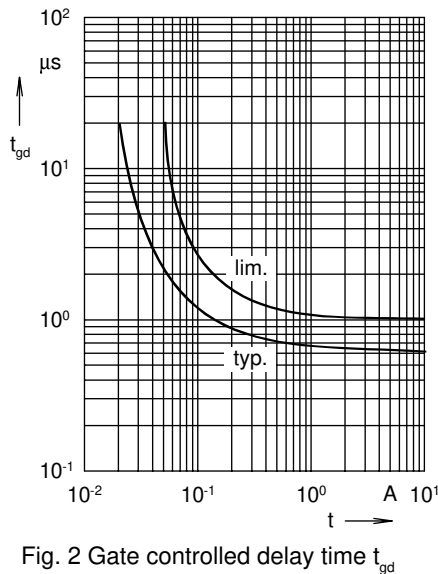


Fig. 2 Gate controlled delay time t_{gd}

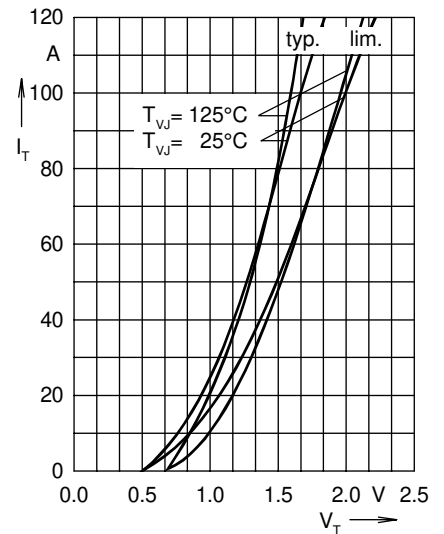


Fig. 3 On-state characteristics

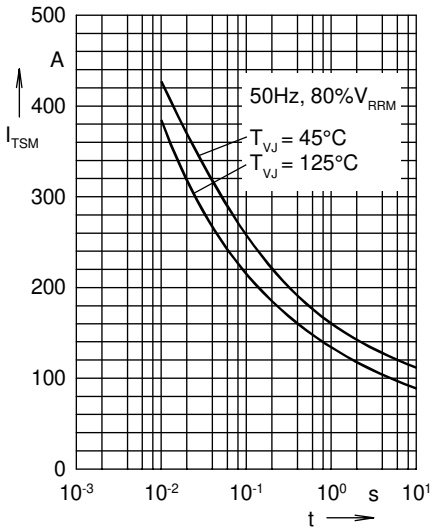


Fig. 4 Surge overload current
 I_{TSM} : crest value, t: duration

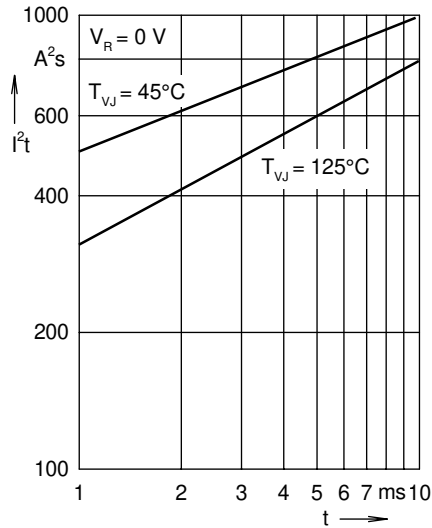


Fig. 5 I^2t versus time (1-10 ms)

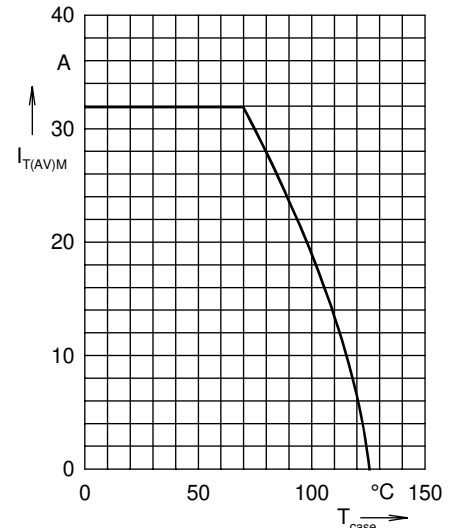


Fig. 6 Maximum forward current at case temperature 180° sine

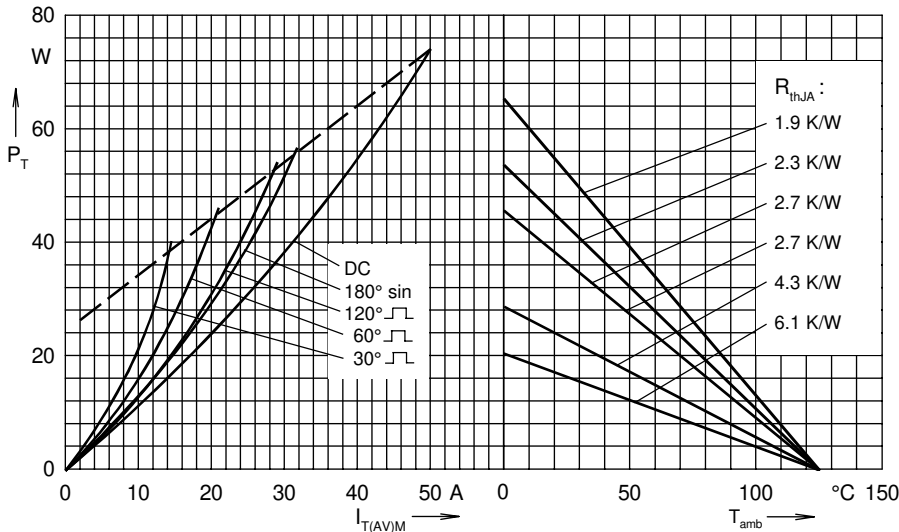


Fig. 7 Power dissipation versus on-state current and ambient temperature

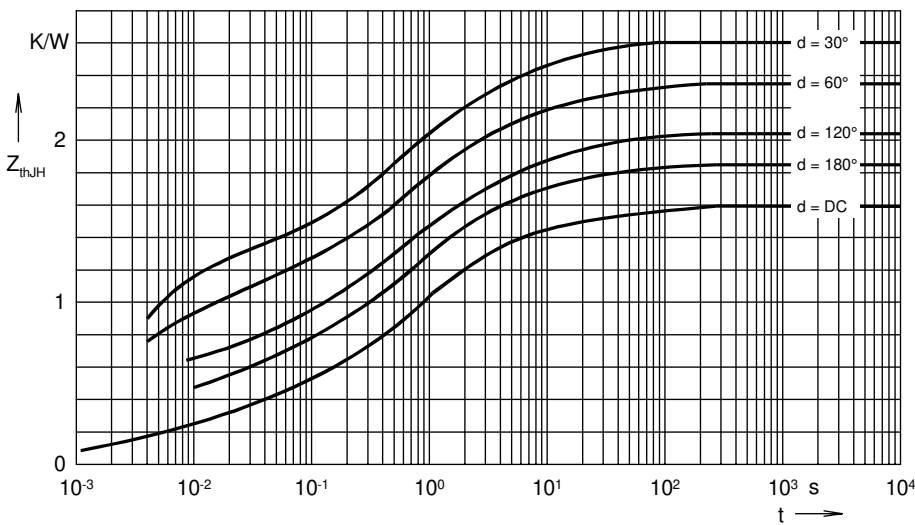


Fig. 8 Transient thermal impedance junction to heatsink

R_{thJH} for various conduction angles d:

d	R_{thJH} (K/W)
DC	1.61
180°	1.85
120°	2.03
60°	2.35
30°	2.60

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.224	0.003
2	0.132	0.028
3	0.321	0.216
4	0.522	1.1
5	0.249	4.2
6	0.162	43.2